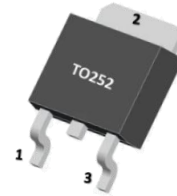


DESCRIPTION

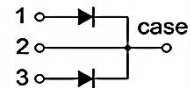
The MBR1065CT meet the ROHS and Green Product requirement with full function reliability approved.

FEATURE

- *Schottky Barrier Chip
- *Guard Ring Die Construction for Transient Protection
- *Low Power Loss,High Efficiency
- *High Surge Capability
- *High Current Capability and Low Forward Voltage Drop
- *For Use in Low Voltage, High Frequency Inverters,Free Wheeling, and Polarity Protection Applications



1. ANODE
2. CATHODE
3. ANODE



ABSOLUTE MAXIMUM RATINGS(TA=25°C, unless otherwise specified.)

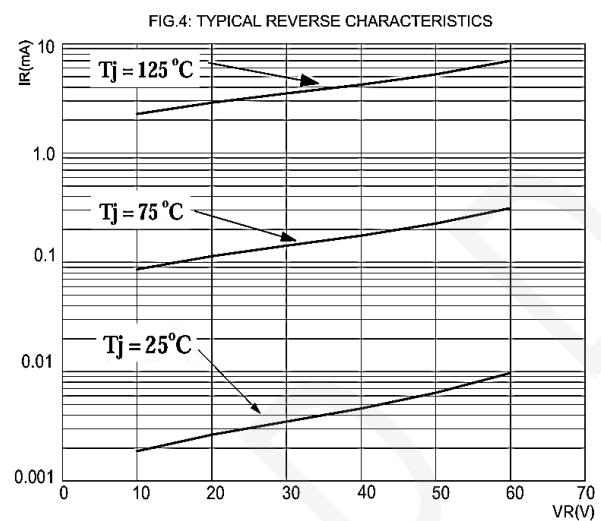
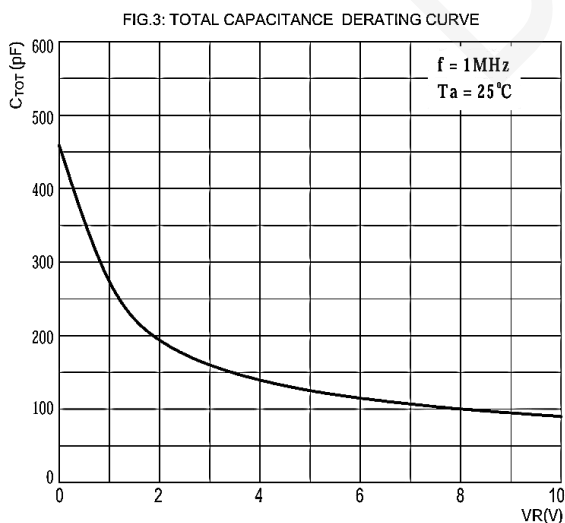
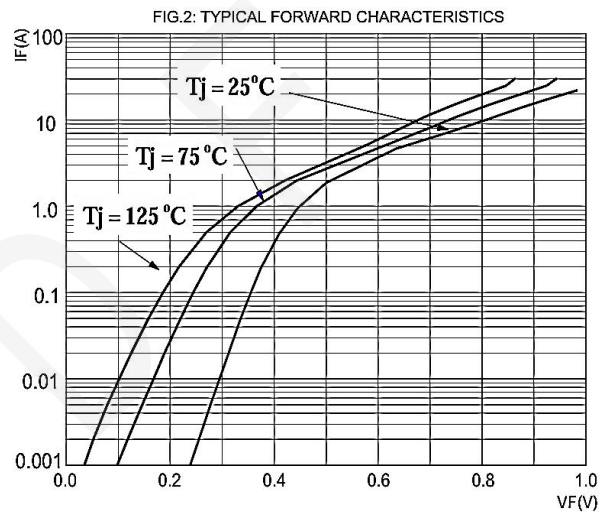
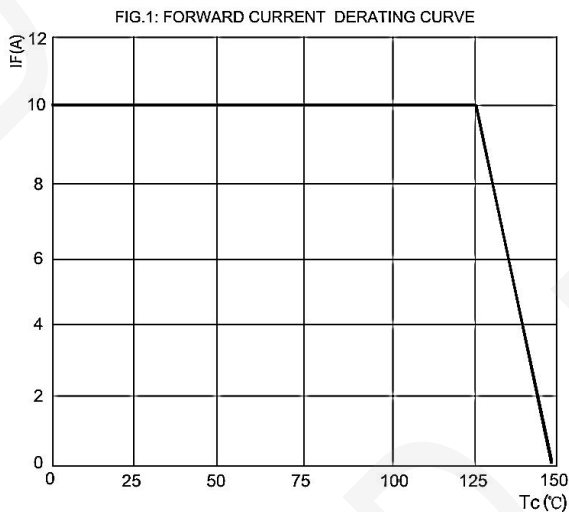
SYMBOL	PARAMETER	VALUE	UNIT
VRRM	Peak repetitive reverse voltage	65	V
VRWM	Working peak reverse voltage	65	V
VR	DC blocking voltage	65	V
VR(RMS)	RMS reverse voltage	45.5	V
IO	Average rectified output current	10	A
IFSM	Non-Repetitive peak forward surge current(8.3ms half sine wave)	100*2	A
Tj	Junction temperature	150	°C
Tstg	Storage temperature	-55~+150	°C
RθJA	Thermal Resistance fromJunction to Ambient	110	°C/W
RθJC	Thermal Resistance From Junction To Case	6	°C/W

Notes: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

ELECTRICAL CHARACTERISTICS (TA=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse voltage	$V_{(BR)}$	$I_R=0.1mA$	65			V
Reverse current	I_R	$V_R=65V$		10	50	μA
Forward voltage	V_{F1}	$I_F=3A$	$T_j=25^\circ C$	0.57		V
	V_{F2}	$I_F=5A$		0.67	0.74	V
	V_{F3}	$I_F=10A$			0.95	V

*Pulse test: pulse width $\leq 300\mu s$, duty cycles $\leq 2.0\%$.

TYPICAL CHARACTERISTICS


■ TO - 252 Package Outline Dimensions

